Next-Generation NAND Flash Part Numbering System

Micron's part numbering system is available at ***www.micron.com/numbering***

Next-Generation NAND Flash*

MT 29F 2G 08 A A A A A WP - xx xx x ES : A

Micron Technology

Single-Supply Flash
29F = NAND Flash
29E = Enterprise NAND Flash

Density
1G = 1Gb
2G = 2Gb
4G = 4Gb
8G = 8Gb
16G = 16Gb
32G = 32Gb
64G = 64Gb
128G = 128Gb
256G = 256Gb

Device Width
01 = 1 bit
08 = 8 bits
16 = 16 bits

Level

Mark	Level
A	SLC
B	Reserved
C	MLC-2

Classification

Mark	Die	nCE	RnB	IO Channels
A	1	0	0	1
B	1	1	1	1
C	2	0	0	1
D	2	1	1	1
E	2	2	2	2
F	2	2	2	1
G				
H	4	1	1	1
J	4	2	2	1
K	4	2	2	2
L	4	4	4	1
M	4	4	4	2
N	4 + 4	2 + 2	2 + 2	1
P	8	1	1	1
Q	8	2	2	1
R	8	2	2	2
T	8	4	4	1
U	8	4	4	2
V				
W				
Y				

Design Revision (shrink)

Production Status
Blank = Production
ES = Engineering Samples
QS = Qualification Samples
MS = Mechanical Sample

Reserved for Future use.

Operating Temperature Range
Blank = Commercial (0°C to +70°C)
IT = Extended (–40°C to +85°C) (AKA ET)
WT = Wireless Temp (–25°C to +85°C)

Speed Grade (Synchronous)
Blank if no speed grade defined
20 = 100MT/s
15 = 133MT/s
12 = 166MT/s

Package Code
WP = 48-pin TSOP I (CPL version) (Pb-free)
WC = 48-pin TSOP I (OCPL version) (Pb-free)
HC = 63-ball VFBGA, 10.5 x 13 x 1.0
C3 = 52-pad ULGA, 12 x 17 x 0.65
C4 = 52-pad VLGA, 12 x 17 x 1.0 (SDP/DDP/QDP)
C5 = 52-pad VLGA, 14 x 18 x 1.0 (SDP/DDP/QDP)
C6 = 52-pad LLGA, 14 x 18 x 1.47 (DDP/QDP/8DP)
C7 = 48-pad LLGA, 12 x 20 x 1.47 (8DP)
C8 = 52-pad WLGA, 14 x 18 x 0.75 (DDP/QDP)
H1 = 100-ball VBGA (Pb-free), 12 x 18 x 1.0
H2 = 100-ball TBGA (Pb-free), 12 x 18 x 1.2
H3 = 100-ball LBGA, (Pb-free) 12 x 18 x 1.4 (DDP/QDP/8DP)
H4 = 63-ball VFBGA, 9 x 11 x 1

Interface

Mark	Interface
A	Async only
B	Sync/Async
D	SPI

Generation Feature Set
A = 1st set of device features
B = 2nd set of device features (rev only if different than 1st set)
C = 3rd set of device features (rev only if different)
D = 4th set of device features (rev only if different)
etc.

Operating Voltage Range
A = 3.3V (2.70–3.60V)
B = 1.8V (1.70–1.95V)
C = 3.3V (2.70–3.60V), VccQ 1.8V (1.70–1.95V)
D = 1.8V (1.65–3.6V) SIM

*Contact Micron for help differentiating between standard and next-generation NAND offerings.

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